

# LM112/LM212/LM312 Operational Amplifiers

# **General Description**

The LM112 series are micropower operational amplifiers with very low offset-voltage and input-current errors—at least a factor of ten better than FET amplifiers over a -55°C to +125°C temperature range. Similar to the LM108 series, that also use supergain transistors, they differ in that they include internal frequency compensation and have provisions for offset adjustment with a single potentiometer.

These amplifiers will operate on supply voltages of  $\pm 2V$  to  $\pm 20V$ , drawing a quiescent current of only 300  $\mu$ A. Performance is not appreciably affected over this range of voltages, so operation from unregulated power sources is easily accomplished. They can also be run from a single supply like the 5V used for digital circuits.

The LM112 series are the first IC amplifiers to improve reliability by including overvoltage protection for the MOS compensation capacitor. Without this feature, IC's have been

known to suffer catastrophic failure caused by short-duration overvoltage spikes on the supplies. Unlike other internally-compensated IC amplifiers, it is possible to overcompensate with an external capacitor to increase stability margin.

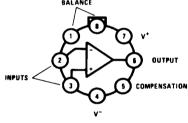
The LM212 is identical to the LM112, except that the LM212 has its performance guaranteed over a  $-25^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$  temperature range instead of  $-55^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ . The LM312 is guaranteed over a  $0^{\circ}\text{C}$  to  $+70^{\circ}\text{C}$  temperature range.

### **Features**

- Maximum input bias current of 3 nA over temperature
- Offset current less than 400 pA over temperature
- Low noise
- Guaranteed drift specifications

## **Connection Diagram**

#### Metal Can Package

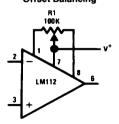


TL/H/7751-4 **Top View** 

Order Number LM112H, LM212H, LM312H or LM112H/883 See NS Package Number H08C

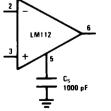
## **Auxiliary Circuits**

## Offset Balancing



### TL/H/7751-2

#### Overcompensation for Greater Stability Margin



TL/H/7751-3

# **Absolute Maximum Ratings**

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

(Note 5)

LM112/LM212 LM312 ± 20V ±18V Supply Voltage 500 mW 500 mW Power Dissipation (Note 1) Differential Input Current (Note 2) ± 10 mA  $\pm$  10 mA Input Voltage (Note 3) ±15V ± 15V Continuous Output Short-Circuit Duration Continuous

Operating Temperature Range

LM112 -55°C to +125°C LM212 -25°C to +85°C 0°C to +70°C

Storage Temperature Range

ESD rating to be determined.

-25°C to +85°C -65°C to +150°C

Lead Temperature (Soldering, 10 sec.)

300°C

-65°C to +150°C 300°C

10°C

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## **Electrical Characteristics** (Note 4)

Parameter	Conditions	LM112/LM212			LM312			Units
		Min	Тур	Max	Min	Тур	Max	J
Input Offset Voltage	T <sub>A</sub> = 25°C		0.7	2.0		2.0	7.5	mV
Input Offset Current	T <sub>A</sub> = 25°C		0.05	0.2		0.2	1	nA
Input Bias Current	T <sub>A</sub> = 25°C		0.8	2.0		1.5	7	nA
Input Resistance	T <sub>A</sub> = 25°C	30	70		10	40		МΩ
Supply Current	T <sub>A</sub> = 25°C		0.3	0.6		0.3	0.8	mA
Large Signal Voltage Gain	$T_A = 25$ °C, $V_S = \pm 15$ V $V_{OUT} = \pm 10$ V, $R_L \ge 10$ kΩ	50	300		25	300		V/mV
Input Offset Voltage				3.0			10	m∨
Average Temperature Coefficient of Input Offset Voltage			3.0	15		6.0	30	μV/°C
Input Offset Current				0.4			1.5	nA
Average Temperature Coefficient of Input Offset Current			0.5	2.5		2.0	10	pA/°C
Input Bias Current				3.0			10	nA
Supply Current	T <sub>A</sub> = 125°C		0.15	0.4				mA
Large Signal Voltage Gain	$V_S = \pm 15V, V_{OUT} = \pm 10V$ $R_L \ge 10 \text{ k}\Omega$	25			15			V/mV
Output Voltage Swing	$V_S = \pm 15V$ , $R_L = 10 \text{ k}\Omega$	± 13	±14		± 13	±14		V
Input Voltage Range	V <sub>S</sub> = ±15V	± 13.5			±14			V
Common-Mode Rejection Ratio		85	100		80	100		₫B
Supply Voltage Rejection Ratio		80	96		80	96		dB

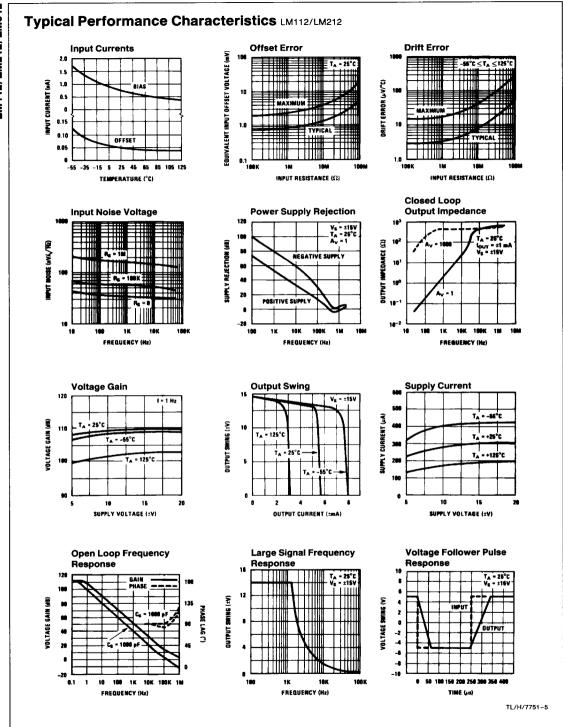
Note 1: The maximum junction temperature of the LM112 is 150°C, LM212 is 100°C and LM312 is 85°C. For operating at elevated temperatures, devices in the H08 package must be derated based on a thermal resistance of 160°C/W, junction to ambient, or 20°C/W, junction to case.

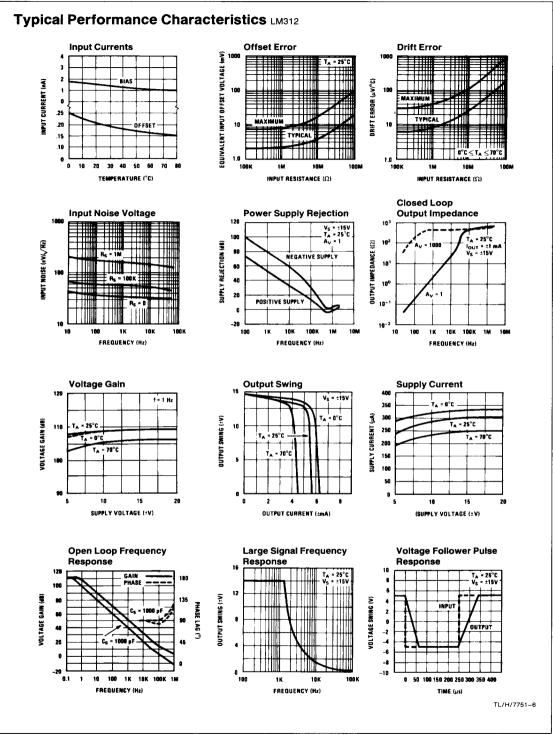
Note 2: The inputs are shunted with shunt diodes for overvoltage protection. Therefore, excessive current will flow if a differential input voltage in excess of 1V is applied between the inputs unless some limiting resistance is used.

Note 3: For supply voltages less than  $\pm$  15V, the absolute maximum input voltage is equal to the supply voltage.

Note 4: These specifications apply for  $\pm 5\text{V} \leq \text{V}_S \leq \pm 20\text{V}$  and  $-55^{\circ}\text{C} \leq \text{T}_A \leq +125^{\circ}\text{C}$  (LM112),  $-25^{\circ}\text{C} \leq \text{T}_A \leq +85^{\circ}\text{C}$  (LM212),  $\pm 5\text{V} \leq \text{V}_S \leq \pm 15\text{V}$  and  $0^{\circ}$  C  $\leq \text{T}_A \leq +70^{\circ}\text{C}$  (LM312) unless otherwise noted.

Note 5: Refer to RETS112X for LM112H military specifications.





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